

Citations for Ion : **Ge**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1964	Sidenius, G. 'Measurement of dE/dX in Gases with Low Energy Heavy Particles' <i>M. R. C. McDowell (Ed.) Atomic Collision Processes, North-Holland, Amsterdam, P. 709-16 (1964)</i> <i>Comment : S. (20-50 keV) Cl, Ga, Zr, Sb, Pb, Fe, Ca, Ge, U -> H2</i>	1964-Side
1965	Chasman, C. Jones, K. W. Ristinen, R. H. 'Measurement of the Energy Loss of Germanium Atoms to Electrons in Germanium at Energies Below 100 keV' <i>Phys. Rev. Letters, 15, 245-48 (1965) (Erratum, Phys. Rev. Letters, 15, 684, (1965))</i> <i>Comment : S, Eta(Epsilon). 20-100 keV Ge -> Ge</i>	1965-Chas
1966	Sattler, A. R. Vook, F. L. Palms, J. H. 'Ionization Produced by Energetic Germanium Atoms Within a Germanium Lattice' <i>Phys. Rev., 143, 588-95 (1966)</i> <i>Comment : S, Eta(Epsilon). 21-997 keV Ge -> Ge</i>	1966-Satt
1966	VanLint, V. A. J. Wyatt, M. E. Schmitt, R. A. Suffredini, C. S. Nichols, D. K. 'Range of Photoparticle Recoil Atoms on Solids' <i>Phys. Rev., 147, 242-48 (1966)</i> <i>Comment : R. (.001- 5 epsilon) Ti, Sc, Cr, Fe, Mn, Ni, Co, Ge, Zr, Y, Sr, Mo, Rh, Pd, Ag, Cd, Sn, Gd, Ta, Au, Th -> Al, Cu</i>	1966-VanL
1967	Chasman, C. Jones, K. W. Ristinen, R. A. Sample, J. T. 'Measurement of Energy Loss of Germanium Atoms to Electrons in Germanium at Energies Below 100 keV' <i>Phys. Rev., 154, 239-44 (1967)</i> <i>Comment : S, Eta(Epsilon). 20-100 keV Ge -> Ge</i>	1967-Chas
1968	Bowman, W. W. Lanzafame, F. M. Cline, C. K. Yu, Yu-Wen Blann, M. 'Recoil Ranges of 0.2 - 5.2 MeV Ions in Vanadium, Nickel, Iron, Zirconium and Gold.' <i>Phys. Rev., 165, 485-93 (1968)</i> <i>Comment : R, dR. Ion(ZI=12-81, E=0.22-5.2 MeV) -> V, Ni, Zr, Au</i>	1968-Bowm
1968	Chasman, C. Jones, K. W. Kramer, H. W. Brandt, W. 'Band-Gap Effects in the Stopping of Ge72* Atoms in Germanium' <i>Phys. Rev. Letters 22, 1430-33 (1968)</i> <i>Comment : S. Eta(Epsilon). 10-30 keV Ge -> Ge</i>	1968-Chas
1968	Hvelplund, P. Fastrup, B. 'Stopping Cross Section in Carbon of 0.2 - 1.5 MeV Atoms with 21 <= Z1 <= 39.' <i>Phys. Rev., 165, 408-14 (1968)</i> <i>Comment : S. (230 - 1470 keV) Sc, Ti, Cr, Mn, Fe, Co, Cu, Ge, Br, W, Y -> C</i>	1968-Hvel2
1971	Jones, K. W. Kraner, H. W. 'Stopping of 1- to 1.8 keV 73Ge Atoms in Germanium.' <i>Phys. Rev. C, 4, 125-29 (1971)</i> <i>Comment : S. Eta(Epsilon) 1-1.8 keV 73Ge -> Ge</i>	1971-Jone

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1975	Feuerstein, A. Kalbitzer, S. Oetzmann, H. 'Range Parameters of Heavy Ions at 10 and 35 keV in Silicon' <i>Phys. Letters A, 51, 165-66 (1975)</i> <i>Comment : R, dR. 10-35 keV Ge, As -> Si</i>	1975-Feue
1975	Holmen, G. Buren, A. Hogberg, P. 'Radiation Damage in Ge Produced and Removed by Energetic Ge Ions' <i>Rad. Effects, 24, 51-8 (1975)</i> <i>Comment : R, dR. Ge (40 KeV) -> Ge</i>	1975-Holm
1975	Jones, K. W. Kraner, H. W. 'Energy Lost to Ionization by 254-Ev ⁷³ Ge Atoms Stopping in Ge' <i>Phys. Rev. A, 11, 1347-53 (1975)</i> <i>Comment : S. Eta(Epsilon) 254 eV ⁷³Ge -> Ge</i>	1975-Jone
1975	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. 'Range Parameters of Heavy Ions in Amorphous Targets at LSS-Energies of 0.0006 < Epsilon < 0.3.' <i>Phys. Letters, 55A, 170-172 (1975)</i> <i>Comment : R, dR. 1-60 keV As, Ge, Sb, Au, Bi -> Si, Ge, Al</i>	1975-Oetz
1976	Benmalek, M. Thomas, J. P. Mackowski, J. M. 'Ion-Bombardment of Amorphous Semiconductors and Related Evolution of Structural and Electrical Properties' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 637-647 (1976)</i> <i>Comment : R. 20-300 keV Ne, Ar, Ge, Cd, Te, Xe, Au -> Ge</i>	1976-Benm
1976	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. 'Range Parameters of Heavy Ions in Silicon and Germanium with Released Energies from 0.01 < epsilon < 10' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 245-54 (1976)</i> <i>Comment : R, dR. (1-40 keV) Al, Sb, As, Ge, Au, Bi -> Si, Ge</i>	1976-Oetz
1977	Surridge, R. K. Sealy, B. J. 'A Comparison of Sn-, Ge-, Se-, and Te-Ion-Implanted GaAs' <i>Appl. Phys., 10, 911-917 (1977)</i> <i>Comment : R. 200 And 300 keV Sn, Ge, Se, Te -> GaAs</i>	1977-Surr
1979	Williamson, K. R. Theis, W. M. Yun, S. S. Park, Y. S. Ehret, J. E. 'Glow-Discharge Optical Spectroscopy Measurement of B-, Ge-, and Mg- Implanted GaAs' <i>J. Appl. Phys., 50, 8019-8024 (1979)</i> <i>Comment : R, dR. 60-120 keV B, Ge, Mg -> GaAs</i>	1979-Will

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1980	Kalbitzer, S. Oetzmann, H. 'Ranges and Range Theories' <i>Rad. Effects, 47, 57-72, (1980)</i> <i>Comment : R, dR. .1-2 MeV Bi, Sb, As, Ge, P, Au, Cs, Eu, Gd Tb -> Si, Ge, C, Al</i>	1980-Kalb
1981	Anthony, J. M. Parker, P. D. Lanford, W. A. 'Z1*3, Z1*4 Corrections to Heavy Ion Energy Loss' <i>IEEE Trans. Nucl. Sci., NS-28, 1227-1229 (1981)</i> <i>Comment : S. Si, Cl, Ti, Fe, Ni, Ge, Br (0.4-2.5 MeV/amu) -> Cu, Ag</i>	1981-Anth2
1982	Anthony, J. M. Lanford, W. A. 'Stopping Power and Effective Charge of Heavy Ions in Solids' <i>Phys. Rev. A, 25 (4), 1868-1879 (1982)</i> <i>Comment : S. C, Si, Cl, Ti, Fe, Ni, Ge, Br, Nb, I (0.1-3.5 MeV/amu) -> C, Al, Cu, Ag, Au</i>	1982-Anth
1996	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. 'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions' <i>Nucl. Inst. Methods, B115, 315-318 (1996)</i> <i>Comment : S. Channeling of ions He to Kr in Si <110></i>	1996-Gelf